

# Ian M Povey

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6165300/publications.pdf>

Version: 2024-02-01

149  
papers

2,869  
citations

172386

29  
h-index

233338

45  
g-index

151  
all docs

151  
docs citations

151  
times ranked

3843  
citing authors

#	ARTICLE	IF	CITATIONS
1	The Langmuir-Blodgett Approach to Making Colloidal Photonic Crystals from Silica Spheres. <i>Advanced Materials</i> , 2010, 22, 3104-3124.	11.1	151
2	Air sensitivity of MoS <sub>2</sub> , MoSe <sub>2</sub> , MoTe <sub>2</sub> , HfS <sub>2</sub> , and HfSe <sub>2</sub> . <i>Journal of Applied Physics</i> , 2016, 120, .	1.1	134
3	Zinc oxide for solar water splitting: A brief review of the material's challenges and associated opportunities. <i>Nano Energy</i> , 2018, 54, 409-428.	8.2	126
4	A broadband cavity ringdown spectrometer for in-situ measurements of atmospheric trace gases. <i>Atmospheric Chemistry and Physics</i> , 2005, 5, 2547-2560.	1.9	104
5	Temperature and frequency dependent electrical characterization of HfO <sub>2</sub> /In <sub>x</sub> Ga <sub>1-x</sub> As interfaces using capacitance-voltage and conductance methods. <i>Applied Physics Letters</i> , 2009, 94, .	1.5	96
6	Broadband cavity ringdown spectroscopy of the NO <sub>3</sub> radical. <i>Chemical Physics Letters</i> , 2001, 342, 113-120.	1.2	80
7	A study of the electrochemical performance of vanadium oxide thin films grown by atmospheric pressure chemical vapour deposition. <i>Solar Energy Materials and Solar Cells</i> , 2011, 95, 2842-2847.	3.0	75
8	Non-covalent Functionalization of Graphene Using Self-Assembly of Alkane-Amines. <i>Advanced Functional Materials</i> , 2012, 22, 717-725.	7.8	73
9	Zinc oxide thin films: Characterization and potential applications. <i>Thin Solid Films</i> , 2010, 518, 4515-4519.	0.8	66
10	The North Atlantic Marine Boundary Layer Experiment (NAMBLEX). Overview of the campaign held at Mace Head, Ireland, in summer 2002. <i>Atmospheric Chemistry and Physics</i> , 2006, 6, 2241-2272.	1.9	65
11	An investigation of capacitance-voltage hysteresis in metal/high-k/In <sub>0.53</sub> Ga <sub>0.47</sub> As metal-oxide-semiconductor capacitors. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	58
12	Erasing diffraction orders: Opal versus Langmuir-Blodgett colloidal crystals. <i>Applied Physics Letters</i> , 2007, 90, 133101.	1.5	53
13	Impact of Forming Gas Annealing on the Performance of Surface-Channel $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ MOSFETs With an ALD $\text{Al}_2\text{O}_3$ Gate Dielectric. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 1084-1090.	1.6	52
14	In situ H <sub>2</sub> S passivation of In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP metal-oxide-semiconductor capacitors with atomic-layer deposited HfO <sub>2</sub> gate dielectric. <i>Applied Physics Letters</i> , 2008, 92, 022902.	1.5	49
15	Analysis of the minority carrier response of n-type and p-type Au/Ni/Al <sub>2</sub> O <sub>3</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP capacitors following an optimized (NH <sub>4</sub> ) <sub>2</sub> S treatment. <i>Applied Physics Letters</i> , 2011, 99, .	1.5	46
16	The Characterization and Passivation of Fixed Oxide Charges and Interface States in the $\text{Al}_2\text{O}_3/\text{InGaAs}$ MOS System. <i>IEEE Transactions on Device and Materials Reliability</i> , 2013, 13, 429-443.	1.5	43
17	Capacitive behavior of Ag doped V <sub>2</sub> O <sub>5</sub> grown by aerosol assisted chemical vapour deposition. <i>Electrochimica Acta</i> , 2016, 196, 294-299.	2.6	41
18	Structural and electrical analysis of the atomic layer deposition of HfO <sub>2</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As capacitors with and without an Al <sub>2</sub> O <sub>3</sub> interface control layer. <i>Applied Physics Letters</i> , 2010, 97, .	1.5	40

#	ARTICLE	IF	CITATIONS
19	The characterisation of aerosol assisted CVD conducting, photocatalytic indium doped zinc oxide films. <i>Journal of Photochemistry and Photobiology A: Chemistry</i> , 2011, 219, 10-15.	2.0	39
20	Enhanced Bragg reflections from size-matched heterostructure photonic crystal thin films prepared by the Langmuir-Blodgett method. <i>Applied Physics Letters</i> , 2006, 89, 093116.	1.5	34
21	Defect-promoted photo-electrochemical performance enhancement of orange-luminescent ZnO nanorod-arrays. <i>Physical Chemistry Chemical Physics</i> , 2017, 19, 12255-12268.	1.3	33
22	Effect of Surface and Defect Chemistry on the Photocatalytic Properties of Intentionally Defect-Rich ZnO Nanorod Arrays. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 17994-18004.	4.0	33
23	Very large phase shift of microwave signals in a 6 nm $\text{HfO}_2/\text{ZrO}_2/\text{HfO}_2$ ferroelectric at $\sim 3$ V. <i>Nanotechnology</i> , 2017, 28, 38LT04.	1.3	32
24	Chemical vapour deposition of $\text{ZrO}_2$ thin films monitored by IR spectroscopy. <i>Journal of Materials Chemistry</i> , 1994, 4, 1815.	6.7	31
25	Electrical analysis of three-stage passivated $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ capacitors with varying $\text{HfO}_2$ thicknesses and incorporating an $\text{Al}_2\text{O}_3$ interface control layer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011, 29, .	0.6	31
26	Atomic layer deposition for the fabrication of 3D photonic crystals structures: Growth of $\text{Al}_2\text{O}_3$ and $\text{VO}_2$ photonic crystal systems. <i>Surface and Coatings Technology</i> , 2007, 201, 9345-9348.	2.2	30
27	Energy barriers at interfaces of (100)GaAs with atomic layer deposited $\text{Al}_2\text{O}_3$ and $\text{HfO}_2$ . <i>Applied Physics Letters</i> , 2008, 93, .	1.5	30
28	Gas phase monitoring of reactions under InP MOVPE growth conditions for the decomposition of tertiarybutyl phosphine and related precursors. <i>Journal of Crystal Growth</i> , 1992, 124, 49-55.	0.7	29
29	Understanding of transmission in the range of high-order photonic bands in thin opal film. <i>Applied Physics Letters</i> , 2008, 92, 191106.	1.5	29
30	Langmuir-Blodgett assembly of colloidal photonic crystals using silica particles prepared without the use of surfactant molecules. <i>Journal of Colloid and Interface Science</i> , 2009, 333, 816-819.	5.0	27
31	A comparison of different spray chemical vapour deposition methods for the production of undoped ZnO thin films. <i>Thin Solid Films</i> , 2009, 518, 1129-1135.	0.8	26
32	Harvesting Electromagnetic Energy in the $\sqrt{V}$ -Band Using a Rectenna Formed by a Bow Tie Integrated With a 6-nm-Thick $\text{Au}/\text{HfO}_2/\text{Pt}$ Metal-Insulator-Metal Diode. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 2973-2980.	1.6	26
33	Structural analysis, elemental profiling, and electrical characterization of $\text{HfO}_2$ thin films deposited on $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ surfaces by atomic layer deposition. <i>Journal of Applied Physics</i> , 2009, 106, 084508.	1.1	25
34	Energy barriers at interfaces between (100) $\text{In}_x\text{Ga}_{1-x}\text{As}$ ( $x=0.53$ ) and atomic-layer deposited $\text{Al}_2\text{O}_3$ and $\text{HfO}_2$ . <i>Applied Physics Letters</i> , 2009, 94, .	1.5	24
35	Low sheet resistance titanium nitride films by low-temperature plasma-enhanced atomic layer deposition using design of experiments methodology. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2014, 32, 031506.	0.9	24
36	Photonic crystal thin films of GaAs prepared by atomic layer deposition. <i>Applied Physics Letters</i> , 2006, 89, 104103.	1.5	23

#	ARTICLE	IF	CITATIONS
37	Diffusion of In <sub>0.53</sub> Ga <sub>0.47</sub> As elements through hafnium oxide during post deposition annealing. Applied Physics Letters, 2014, 104, .	1.5	23
38	Lithographically Defined, Room Temperature Low Threshold Subwavelength Red-Emitting Hybrid Plasmonic Lasers. Nano Letters, 2016, 16, 7822-7828.	4.5	23
39	Spectroscopic Investigation of Zinc-Containing Organometallic Radicals Prepared Using a Pulsed Electrical Discharge Nozzle. The Journal of Physical Chemistry, 1994, 98, 10427-10431.	2.9	22
40	A broadband lidar for the measurement of tropospheric constituent profiles from the ground. Journal of Geophysical Research, 1998, 103, 3369-3380.	3.3	22
41	Electrically active interface defects in the In <sub>0.53</sub> Ga <sub>0.47</sub> As MOS system. Microelectronic Engineering, 2013, 109, 182-188.	1.1	22
42	Aluminum Interdiffusion into LiCoO <sub>2</sub> Using Atomic Layer Deposition for High Rate Lithium Ion Batteries. ACS Applied Energy Materials, 2018, 1, 3277-3282.	2.5	22
43	Optical second harmonic generation studies of the nature of the GaAs(100) surface in air. Journal of Crystal Growth, 1992, 120, 94-97.	0.7	21
44	Quantum beat study of the nuclear hyperfine structure of OD and Ar <sup>+</sup> OD in their A <sup>2</sup> Σ <sup>+</sup> electronic states. Journal of Chemical Physics, 1996, 104, 5365-5373.	1.2	21
45	The incorporation of preformed metal nanoparticles in zinc oxide thin films using aerosol assisted chemical vapour deposition. Thin Solid Films, 2010, 518, 6921-6926.	0.8	21
46	Structural and Electrical Properties of HfO <sub>2</sub> /n-In <sub>x</sub> Ga <sub>1-x</sub> As structures (x: 0, 0.1, 0.2, 0.3, 0.4, 0.5, 0.6, 0.7, 0.8, 0.9, 1.0). Journal of Applied Physics, 2010, 107, 093701.	0.3	20
47	Back-gated Nb-doped MoS <sub>2</sub> junctionless field-effect-transistors. AIP Advances, 2016, 6, .	0.6	20
48	Examining the relationship between capacitance-voltage hysteresis and accumulation frequency dispersion in InGaAs metal-oxide-semiconductor structures based on the response to post-metal annealing. Microelectronic Engineering, 2017, 178, 204-208.	1.1	20
49	Observation of peripheral charge induced low frequency capacitance-voltage behaviour in metal-oxide-semiconductor capacitors on Si and GaAs substrates. Journal of Applied Physics, 2012, 111, .	1.1	19
50	The impact of forming gas annealing on the electrical characteristics of sulfur passivated Al <sub>2</sub> O <sub>3</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As (110) metal-oxide-semiconductor capacitors. Applied Physics Letters, 2017, 110, 142905.	1.5	19
51	Engineered Light Scattering in Colloidal Photonic Heterocrystals. Advanced Functional Materials, 2010, 20, 853-860.	7.8	18
52	Electrical and physical characterization of the Al <sub>2</sub> O <sub>3</sub> /p-GaSb interface for 1%, 5%, 10%, and 22% (NH <sub>4</sub> ) <sub>2</sub> S surface treatments. Applied Physics Letters, 2014, 105, 162907.	1.5	18
53	Island Coalescence during Film Growth: An Underestimated Limitation of Cu ALD. Advanced Materials Interfaces, 2017, 4, 1700274.	1.9	18
54	A RHEED and reflectance anisotropy study of the MBE growth of GaAs, AlAs and InAs on GaAs(001). Surface Science, 1992, 274, 263-269.	0.8	17

#	ARTICLE	IF	CITATIONS
55	Novel photonic crystal thin films using the Langmuir-Blodgett approach. <i>Physica B: Condensed Matter</i> , 2007, 394, 233-237.	1.3	17
56	Plasma enhanced atomic layer deposition of copper: A comparison of precursors. <i>Surface and Coatings Technology</i> , 2013, 230, 3-12.	2.2	17
57	Progression towards high efficiency perovskite solar cells via optimisation of the front electrode and blocking layer. <i>Journal of Materials Chemistry C</i> , 2016, 4, 11269-11277.	2.7	17
58	Mechanisms of Pyrolysis of Tricarbonylcyclopentadienylmanganese and Tricarbonyl(methylcyclopentadienyl)manganese. <i>Organometallics</i> , 1995, 14, 3717-3723.	1.1	16
59	Junctionless nanowire transistor fabricated with high mobility Ge channel. <i>Physica Status Solidi - Rapid Research Letters</i> , 2014, 8, 65-68.	1.2	16
60	Surface Oxide Characterization and Interface Evolution in Atomic Layer Deposition of Al <sub>2</sub> O <sub>3</sub> on InP(100) Studied by in Situ Infrared Spectroscopy. <i>Journal of Physical Chemistry C</i> , 2014, 118, 5862-5871.	1.5	16
61	Atomic layer deposition of Cu with a carbene-stabilized Cu(silylamide). <i>Journal of Materials Chemistry C</i> , 2014, 2, 9205-9214.	2.7	16
62	Broadband lidar measurements of tropospheric water vapor profiles. <i>Journal of Geophysical Research</i> , 1998, 103, 31191-31202.	3.3	15
63	2.55ÅGHz miniaturised phased antenna array based on 7Ånm-thick Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> ferroelectrics. <i>Electronics Letters</i> , 2018, 54, 469-470.	0.5	15
64	Wafer-scale very large memory windows in graphene monolayer/HfZrO ferroelectric capacitors. <i>Nanotechnology</i> , 2018, 29, 425204.	1.3	15
65	Multifunctionalities of 2D MoS <sub>2</sub> self-switching diode as memristor and photodetector. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2021, 126, 114451.	1.3	15
66	Quantum beat spectroscopy of jet-cooled transient radicals generated by a pulsed electrical discharge. <i>Chemical Physics Letters</i> , 1996, 248, 470-475.	1.2	14
67	Nucleation and Chemical Transformation of RuO <sub>2</sub> Films Grown on (100) Si Substrates by Atomic Layer Deposition. <i>Chemical Vapor Deposition</i> , 2011, 17, 114-122.	1.4	14
68	High aspect ratio iridescent three-dimensional metal-insulator-metal capacitors using atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015, 33, .	0.9	14
69	Large-area growth of MoS <sub>2</sub> at temperatures compatible with integrating back-end-of-line functionality. <i>2D Materials</i> , 2021, 8, 025008.	2.0	14
70	The pyrolysis of precursors for GaAs MOCVD studied by in-situ and ex-situ Fourier transform infrared spectroscopy. <i>Journal of Crystal Growth</i> , 1992, 124, 10-15.	0.7	12
71	Do gas phase adducts form during metalorganic vapour phase epitaxial growth of gallium arsenide?. <i>Journal of Crystal Growth</i> , 1994, 145, 104-112.	0.7	12
72	A study of capacitance-voltage hysteresis in the HfO <sub>2</sub> /InGaAs metal-oxide-semiconductor system. <i>Microelectronic Engineering</i> , 2015, 147, 273-276.	1.1	12

#	ARTICLE	IF	CITATIONS
73	Optical monitoring of deposition and decomposition processes in MOCVD and MBE using reflectance anisotropy. <i>Journal of Crystal Growth</i> , 1992, 124, 37-43.	0.7	11
74	Probing surface chemical processes during epitaxial semiconductor crystal growth at near-atmospheric pressures using photon-based techniques. <i>Faraday Discussions</i> , 1993, 95, 199.	1.6	11
75	A comparison of the GaAs atomic layer deposition infiltration of photonic crystals engineered by the controlled evaporation and Langmuir-Blodgett methods. <i>Thin Solid Films</i> , 2008, 517, 811-813.	0.8	11
76	Band offsets at interfaces of (100)In <sub>x</sub> Ga <sub>1-x</sub> As (0 ≤ x ≤ 0.53) with Al <sub>2</sub> O <sub>3</sub> and HfO <sub>2</sub> . <i>Microelectronic Engineering</i> , 2009, 86, 1550-1553.	1.1	11
77	Capacitance and Conductance for an MOS System in Inversion, with Oxide Capacitance and Minority Carrier Lifetime Extractions. <i>IEEE Transactions on Electron Devices</i> , 2014, 61, 4176-4185.	1.6	11
78	Electrochemical evaluation of vanadium pentoxide coatings grown by AACVD. <i>Solar Energy Materials and Solar Cells</i> , 2015, 143, 601-605.	3.0	11
79	Rapid low-temperature solution growth of ZnO:Co nanorod arrays with controllable visible light absorption. <i>CrystEngComm</i> , 2017, 19, 1938-1946.	1.3	10
80	MoS <sub>2</sub> radio: detecting radio waves with a two-dimensional transition metal dichalcogenide semiconductor. <i>Nanotechnology</i> , 2020, 31, 06LT01.	1.3	10
81	The Kinetics and Mechanism of the Pyrolysis of Manganese and Manganese Silicide CVD Precursors. <i>Chemical Vapor Deposition</i> , 1998, 04, 103-107.	1.4	10
82	Developments in the Understanding of ALD Processes and Applications of ALD in Critical Technologies. <i>ECS Transactions</i> , 2007, 11, 155-166.	0.3	9
83	Modification of emission of CdTe nanocrystals by the local field of Langmuir-Blodgett colloidal photonic crystals. <i>Journal of Applied Physics</i> , 2008, 104, 103118.	1.1	9
84	Structural and Electrical Analysis of Thin Interface Control Layers of MgO or Al <sub>2</sub> O <sub>3</sub> Deposited by Atomic Layer Deposition and Incorporated at the High-k/III-V Interface of MO <sub>2</sub> /In <sub>x</sub> Ga <sub>1-x</sub> As (M = Hf   Zr, x = 0   0.53) Gate Stacks. <i>ECS Transactions</i> , 2010, 33, 69-82.	0.3	9
85	Infrared and near-infrared spectroscopic probing of atomic layer deposition processes. <i>Journal of Molecular Structure</i> , 2010, 976, 324-327.	1.8	9
86	Nonhomogeneous spatial distribution of filamentary leakage current paths in circular area Pt/HfO <sub>2</sub> /Pt capacitors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013, 31, 01A107.	0.6	9
87	A bottom-up fabrication method for the production of visible light active photonic crystals. <i>Journal of Materials Chemistry C</i> , 2014, 2, 1675-1682.	2.7	9
88	(Invited) Equivalent Oxide Thickness Correction in the High-k/In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP System. <i>ECS Transactions</i> , 2010, 33, 433-444.	0.3	8
89	Silicon nanocrystals: Novel synthesis routes for photovoltaic applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013, 210, 649-657.	0.8	8
90	Atomic Layer Deposited Electron Transport Layers in Efficient Organometallic Halide Perovskite Devices. <i>MRS Advances</i> , 2018, 3, 3075-3084.	0.5	8

#	ARTICLE	IF	CITATIONS
91	Combinatorial ALD for the growth of ZnO/TiO <sub>2</sub> nanolaminates and mixed ZnO/TiO <sub>2</sub> nanostructured films. <i>Materials Advances</i> , 2022, 3, 2896-2907.	2.6	8
92	Schiff base precursor compounds for the chemical beam epitaxy of oxide thin films. I. Deposition of CuO on MgO[001] using copper (II) bis(benzoylacetone)ethylenediimine. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1996, 14, 3208-3213.	0.9	7
93	The Kinetics and Mechanism of the Pyrolysis of Manganese and Manganese Silicide CVD Precursors. <i>Chemical Vapor Deposition</i> , 1998, 4, 103-107.	1.4	7
94	Investigation of bulk defects in amorphous and crystalline HfO <sub>2</sub> thin films. <i>Microelectronic Engineering</i> , 2011, 88, 1499-1502.	1.1	7
95	The structural and electrical properties of the SrTa <sub>2</sub> O <sub>6</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP system. <i>Microelectronic Engineering</i> , 2011, 88, 1054-1057.	1.1	7
96	The role of local chemical hardness and van der Waals interactions in the anionic polymerization of alkyl cyanoacrylates. <i>Polymer Chemistry</i> , 2016, 7, 3236-3243.	1.9	7
97	Structural and electrical characterisation of PtS from H <sub>2</sub> S-converted Pt. <i>Applied Materials Today</i> , 2021, 25, 101163.	2.3	7
98	Mechanisms of pyrolysis of organometallic deposition precursors. <i>Journal of Materials Chemistry</i> , 1994, 4, 13.	6.7	6
99	Gallium Arsenide Infiltration of Nanoporous Multilayers: A Route to High-Dielectric Contrast One-Dimensional Photonic Crystals. <i>Small</i> , 2010, 6, 1283-1287.	5.2	6
100	Investigation of electron mobility in surface-channel Al <sub>2</sub> O <sub>3</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As MOSFETs. <i>Solid-State Electronics</i> , 2013, 88, 37-42.	0.8	6
101	ZnO Nanorod-Arrays as Photo-(Electro)Chemical Materials: Strategies Designed to Overcome the Material's Natural Limitations. <i>Journal of the Electrochemical Society</i> , 2018, 165, H3034-H3044.	1.3	6
102	Electromagnetic energy harvesting based on HfZrO tunneling junctions. <i>Nanotechnology</i> , 2018, 29, 445203.	1.3	6
103	Reply to comments on "optical second harmonic generation studies of the nature of the GaAs (100) surface in the air". <i>Journal of Crystal Growth</i> , 1993, 130, 323-324.	0.7	5
104	Decomposition of Cyanoethylphosphine, Benzylphosphine, and Cyclopentylphosphine during InP MOCVD Growth Studied by FTIR Spectroscopy: Criteria for the Design of Organophosphine Precursors. <i>Journal of the Electrochemical Society</i> , 1994, 141, 1886-1893.	1.3	5
105	Benzoylpivaloylmethanide Precursors for the Chemical Beam Epitaxy of Oxide Thin Films. 1. Synthesis, Characterization, and Use of Yttrium Benzoylpivaloylmethanide. <i>Chemistry of Materials</i> , 1997, 9, 127-134.	3.2	5
106	In-Situ Probing of Atomic Layer Deposition Processes using Infrared and Near Infrared Spectroscopy. <i>ECS Transactions</i> , 2008, 16, 349-354.	0.3	5
107	The effect of dopants on the morphology, microstructure and electrical properties of transparent zinc oxide films prepared by the sol-gel method. <i>Thin Solid Films</i> , 2011, 520, 1174-1177.	0.8	5
108	Junctionless InGaAs MOSFETs with InAlAs barrier isolation and channel thinning by digital wet etching., 2013, , .		5



#	ARTICLE	IF	CITATIONS
109	Effects of alternating current voltage amplitude and oxide capacitance on mid-gap interface state defect density extractions in In <sub>0.53</sub> Ga <sub>0.47</sub> As capacitors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2013, 31, 01A119.	0.6	5
110	Role of Interfacial Aluminum Silicate and Silicon as Barrier Layers for Atomic Layer Deposition of Al <sub>2</sub> O <sub>3</sub> Films on Chemically Cleaned InP(100) Surfaces. Journal of Physical Chemistry C, 2014, 118, 29164-29179.	1.5	5
111	Band offsets and trap-related electron transitions at interfaces of (100)InAs with atomic-layer deposited Al <sub>2</sub> O <sub>3</sub> . Journal of Applied Physics, 2016, 120, 235701.	1.1	5
112	Inversion in the In <sub>0.53</sub> Ga <sub>0.47</sub> As metal-oxide-semiconductor system: Impact of the In <sub>0.53</sub> Ga <sub>0.47</sub> As doping concentration. Applied Physics Letters, 2017, 110, 032902.	1.5	5
113	Reflectance anisotropy from (001) GaAs surfaces during pseudo-ALE growth of GaAs. Applied Surface Science, 1993, 69, 46-51.	3.1	4
114	X-ray optics developments at ESA. , 2013, , .		4
115	Effect of forming gas annealing on the inversion response and minority carrier generation lifetime of n and p-In <sub>0.53</sub> Ga <sub>0.47</sub> As MOS capacitors. Microelectronic Engineering, 2015, 147, 325-329.	1.1	4
116	Next generation low temperature polycrystalline materials for above IC electronics. High mobility n- and p-type III-V metalorganic vapour phase epitaxy thin films on amorphous substrates. JPhys Photonics, 2020, 2, 025003.	2.2	4
117	The use of hex-5-enylarsine as a chemically designed precursor to probe the mechanisms of the metalorganic vapour phase epitaxy growth of gallium arsenide; consequences for reactor design. Journal of Crystal Growth, 1994, 137, 347-354.	0.7	3
118	Indium tin oxide-silicon nanocrystal nanocomposite grown by aerosol assisted chemical vapour deposition. Journal of Sol-Gel Science and Technology, 2015, 73, 666-672.	1.1	3
119	Structural and Electronic Properties of Polycrystalline InAs Thin Films Deposited on Silicon Dioxide and Glass at Temperatures below 500 Å°C. Crystals, 2021, 11, 160.	1.0	3
120	A Slot-Die Technique for the Preparation of Continuous, High-Area, Chitosan-Based Thin Films. Polymers, 2021, 13, 1566.	2.0	3
121	Optoacoustic characterization of synthetic opals. Journal of Physics: Conference Series, 2007, 92, 012030.	0.3	2
122	Photonic band gap thin films from mesoporous silica spheres acting as receptacles for species yielding added functionality. Photonics and Nanostructures - Fundamentals and Applications, 2007, 5, 91-95.	1.0	2
123	Improved reliability of Al<sub>2</sub>O<sub>3</sub>/InGaAs/InP MOS structures through in-situ forming gas annealing. , 2012, , .		2
124	A combined capacitance-voltage and hard x-ray photoelectron spectroscopy characterisation of metal/Al <sub>2</sub> O <sub>3</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As capacitor structures. Journal of Applied Physics, 2014, 116, 024104.	1.1	2
125	Hall-effect mobility for a selection of natural and synthetic 2D semiconductor crystals. , 2017, , .		2
126	Current rectification effects in 6-nm thick Hf Zr <sub>1-Oy</sub> ferroelectrics/Si planar heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2018, 104, 241-246.	1.3	2



#	ARTICLE	IF	CITATIONS
127	Microwave applications of zirconium-doped hafnium oxide ferroelectrics: from nanoscale calculations up to experimental results. , 2020, , .		2
128	A multi-purpose pilot-scale molten metal & molten salt pyrolysis reactor. MethodsX, 2022, 9, 101606.	0.7	2
129	Bleaching-induced evolution of directional emission from dye-loaded opals. Journal of Optics, 2008, 10, 115201.	1.5	1
130	Scalable high-k metal-insulator-metal capacitors with low leakage, high breakdown fields and improved voltage linearity. Electronics Letters, 2012, 48, 230.	0.5	1
131	(Invited) Can Metal/Al <sub>2</sub> O <sub>3</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP MOSCAP Properties Translate to Metal/Al <sub>2</sub> O <sub>3</sub> /In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP MOSFET Characteristics. ECS Transactions, 2012, 45, 79-88.	0.3	1
132	Uniform coating of high aspect ratio surfaces through atomic layer deposition. , 2012, , .		1
133	Study of interface and oxide defects in high-k/In<inf>0.53</inf>/Ga<inf>0.47</inf>/As n-MOSFETs. , 2012, , .		1
134	A study of capacitance-voltage hysteresis in HfO<inf>2</inf>/InGaAs metal-oxide-semiconductor systems. , 2014, , .		1
135	(Invited) Tailoring Zinc Oxide Nanorod-Arrays for Photo-(electro)Chemical Applications. ECS Transactions, 2017, 77, 43-60.	0.3	1
136	Reconfigurable horizontal&vertical carrier transport in graphene/HfZrO field-effect transistors. Nanotechnology, 2020, 31, 025203.	1.3	1
137	Broadband CCD detection system for rotational Raman lidar studies of the troposphere. , 2001, 4153, 657.		0
138	Langmuir-Blodgett Approach Versus Self-Organization in Realization of Colloidal Photonic Crystals and Hetero-Crystals - Pros and Cons. , 2007, , .		0
139	Transmission spectrum transformation at photonic hetero-crystal interfaces &#x2014; Polarization anisotropy. , 2008, , .		0
140	Light transmission and scattering in engineered colloidal hetero-crystals. Proceedings of SPIE, 2008, , .	0.8	0
141	The Effects of Using ALD-Grown ZnO Buffer Layers on the Properties of Indium Tin Oxide Grown by Chemical Solution Deposition. Journal of Nanoscience and Nanotechnology, 2011, 11, 8354-8357.	0.9	0
142	Selected Peer-Reviewed Articles from The EuroCVD-18 Conference (EuroCVD 2011). Journal of Nanoscience and Nanotechnology, 2011, 11, 7945-7947.	0.9	0
143	Electrical Properties and Charge Transport in the Pd/Al <sub>2</sub> O <sub>3</sub> /InGaAs MOS Structure. ECS Transactions, 2013, 58, 379-384.	0.3	0
144	Atomic Layer Deposition on Fabrics for Flame Resistance. ECS Transactions, 2015, 66, 31-35.	0.3	0

#	ARTICLE	IF	CITATIONS
145	Indium Tin Oxide - Silicon Nanocrystal Nanocomposite Grown by Aerosol-Assisted Chemical Vapour Deposition. ECS Transactions, 2015, 66, 17-21.	0.3	0
146	Influence of Substrate on Hafnium Silicate Metal-Insulator-Metal Capacitors Grown by Atomic Layer Deposition. ECS Transactions, 2015, 66, 269-275.	0.3	0
147	Growth of V <sub>2</sub> O <sub>5</sub> Films for Battery Applications by Pulsed Chemical Vapor Deposition. ECS Transactions, 2018, 85, 83-94.	0.3	0
148	One-Pot Synthesis of Co(OH) <sub>2</sub> and/or Co <sub>3</sub> O <sub>4</sub> Decorated Cobalt-Doped ZnO Nanorod Arrays and Their Potential as (Photo)Anode Materials. ChemistrySelect, 2019, 4, 5033-5043.	0.7	0
149	Chemical Vapor Deposition of MoS <sub>2</sub> for Back-End-of-Line Applications. ECS Meeting Abstracts, 2021, MA2021-02, 1952-1952.	0.0	0